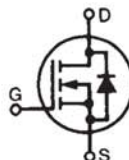


Linear Power MOSFET w/Extended FBSOA

IXTK8N150L IXTX8N150L

N-Channel Enhancement Mode
Guaranteed FBSOA



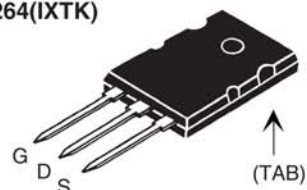
$$V_{DSS} = 1500V$$

$$I_{D25} = 8A$$

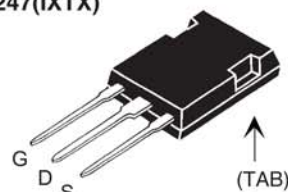
$$R_{DS(on)} \leq 3.6\Omega$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^{\circ}C$ to $150^{\circ}C$	1500	V
V_{DGR}	$T_J = 25^{\circ}C$ to $150^{\circ}C$, $R_{GS} = 1M\Omega$	1500	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^{\circ}C$	8	A
I_{DM}	$T_C = 25^{\circ}C$, Pulse Width Limited by T_{JM}	20	A
P_D	$T_C = 25^{\circ}C$	700	W
T_J		-55 to +150	$^{\circ}C$
T_{JM}		150	$^{\circ}C$
T_{stg}		-55 to +150	$^{\circ}C$
T_L	1.6mm (0.063 in.) from Case for 10s	300	$^{\circ}C$
T_{SOLD}	Plastic Body for 10s	260	$^{\circ}C$
M_d	Mounting Torque (IXTK)	1.13/10	Nm/lb.in.
F_C	Mounting Force (IXTX)	20..120 / 4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

TO-264(IXTK)



PLUS247(IXTX)



G = Gate D = Drain
S = Source TAB = Drain

Features

- Designed for Linear Operations
- International Standard Packages
- Guaranteed FBSOA at $60^{\circ}C$
- Molding Epoxies Meet UL94 V-0 Flammability Classification

Applications

- Programmable Loads
- Current Regulators
- DC-DC Convertors
- Battery Chargers
- DC Choppers
- Temperature and Lighting Controls

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Symbol	Test Conditions ($T_J = 25^{\circ}C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 1mA$	1500		
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	5.0		8.0
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0V$ $T_J = 125^{\circ}C$			50 μA 3 mA
$R_{DS(on)}$	$V_{GS} = 20V$, $I_D = 0.5 \cdot I_{D25}$, Note 1			3.6 Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 50\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	1.4	2.3	3.2
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		8000	pF
C_{oss}			405	pF
C_{rss}			70	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 15\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 2\Omega$ (External)		36	ns
t_r			18	ns
$t_{d(off)}$			90	ns
t_f			95	ns
$Q_{g(on)}$	$V_{GS} = 15\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		250	nC
Q_{gs}			80	nC
Q_{gd}			116	nC
R_{thJC}			0.15	0.18°C/W
R_{thCS}				$^\circ\text{C/W}$

Safe Operating Area Specification

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
SOA	$V_{DS} = 1000\text{V}$, $I_D = 0.5\text{A}$, $T_C = 60^\circ\text{C}$, $T_p = 3\text{s}$	500		W

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			8
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			32
V_{SD}	$I_F = 8\text{A}$, $V_{GS} = 0\text{V}$, Note 1			1.2
t_{rr}	$I_F = I_S$, $-di/dt = 100\text{A}/\mu\text{s}$, $V_R = 100\text{V}$		1700	ns

Notes: 1. Pulse Test, $t \leq 300\mu\text{s}$; Duty Cycle, $d \leq 2\%$.

PRELIMINARY TECHNICAL INFORMATION

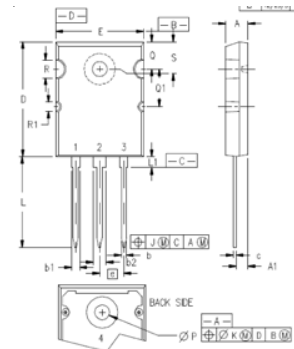
The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

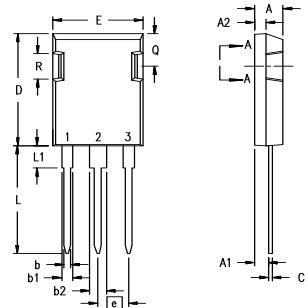
TO-264 (IXTK) Outline



1 - GATE
2, 4 - DRAIN (COLLECTOR)
3 - SOURCE (EMITTER)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

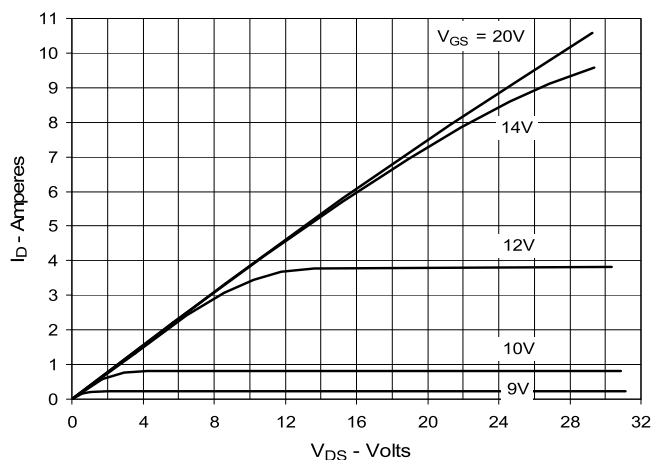
PLUS 247™ (IXTX) Outline



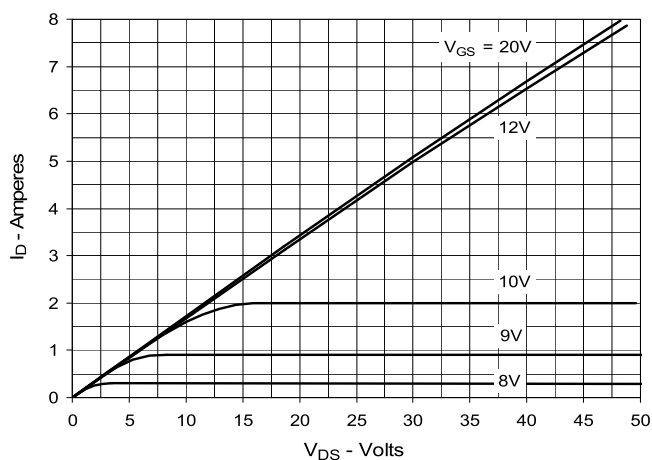
Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

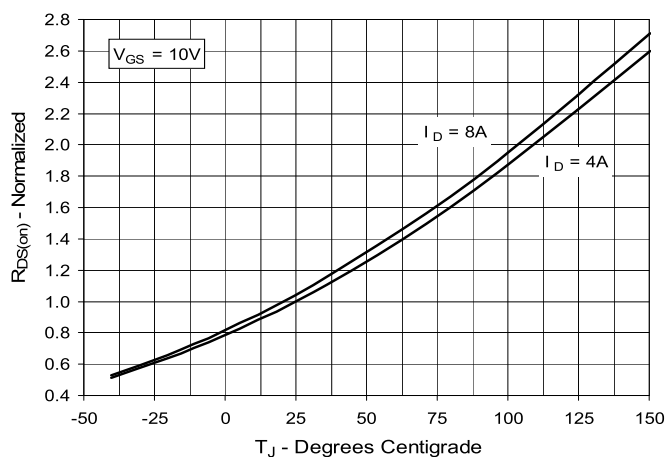
**Fig. 1. Extended Output Characteristics
@ 25°C**



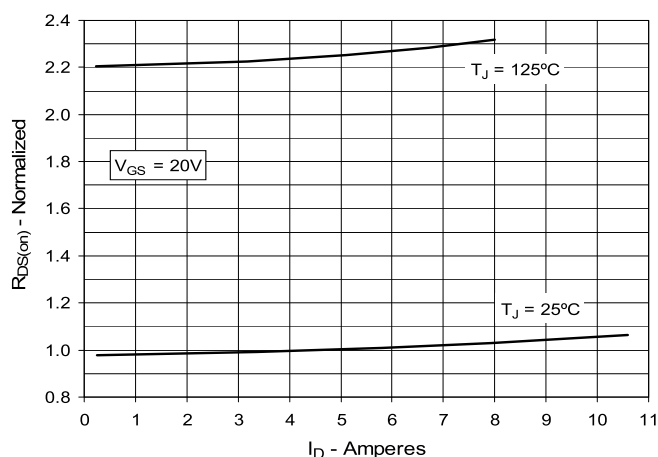
**Fig. 2. Output Characteristics
@ 125°C**



**Fig. 3. $R_{DS(on)}$ Normalized to $I_D = 4\text{A}$ Value
vs. Junction Temperature**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 4\text{A}$ Value
vs. Drain Current**



**Fig. 5. Maximum Drain Current vs.
Case Temperature**

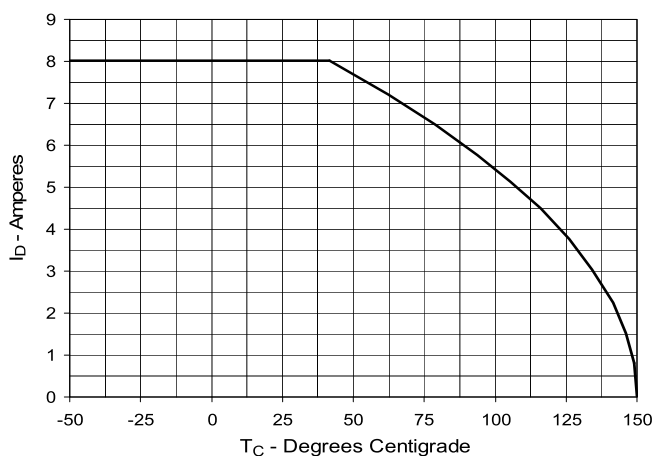


Fig. 6. Input Admittance

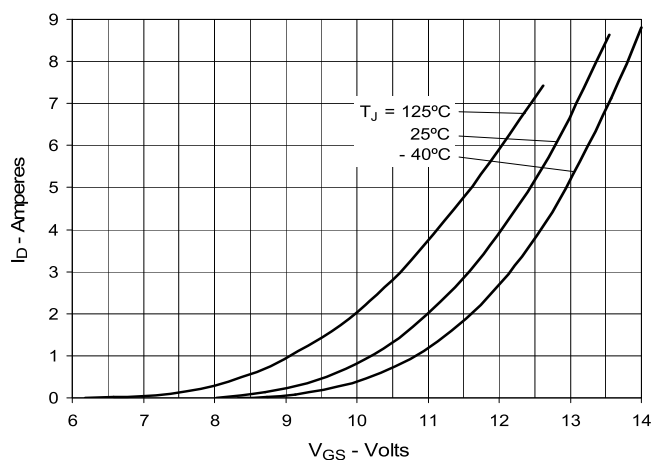


Fig. 7. Transconductance

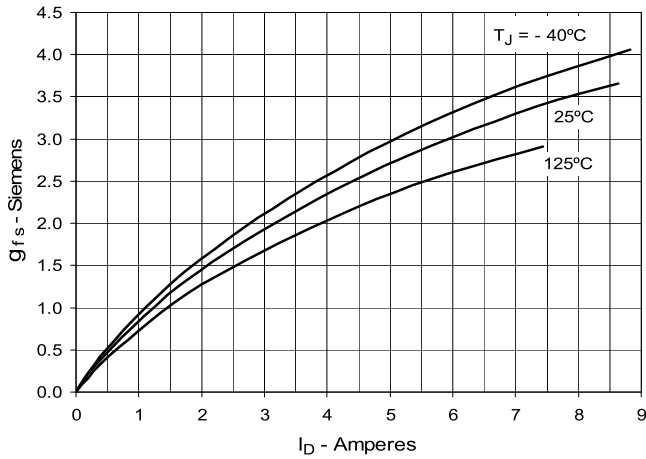


Fig. 8. Forward Voltage Drop of Intrinsic Diode

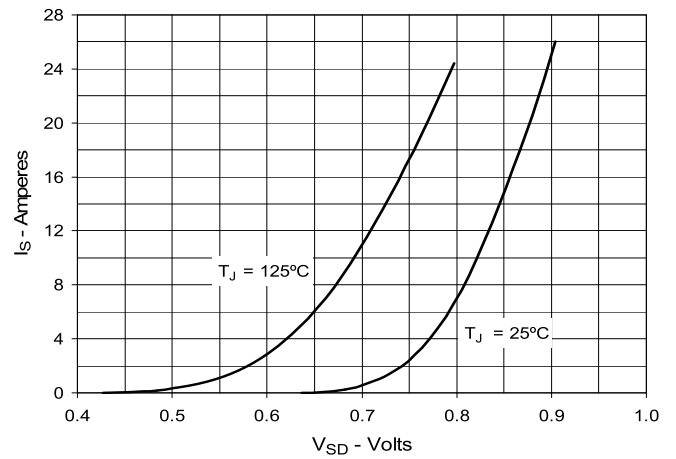


Fig. 9. Gate Charge

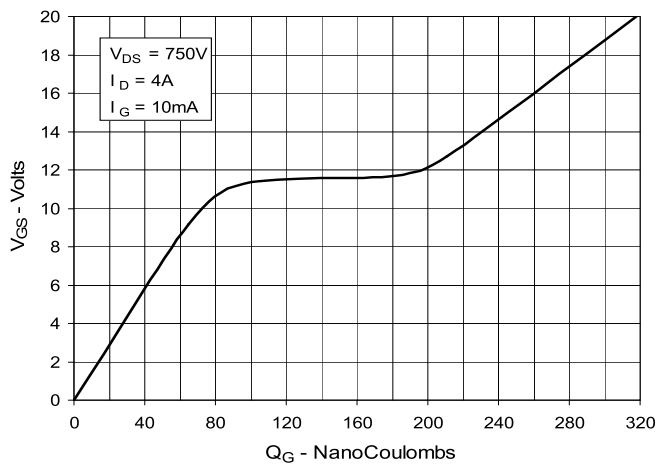


Fig. 10. Capacitance

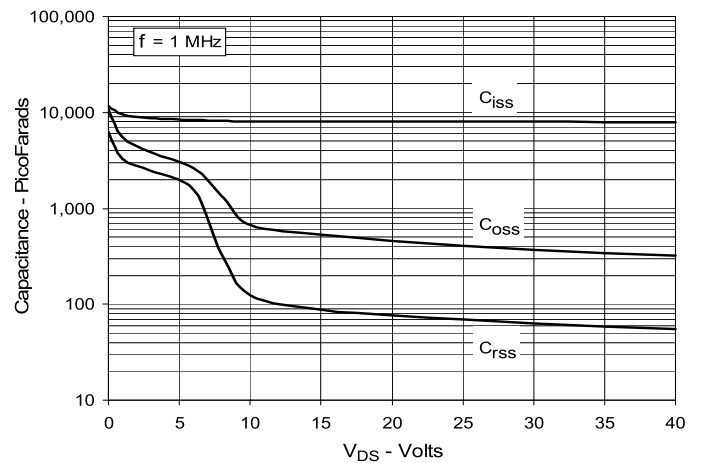
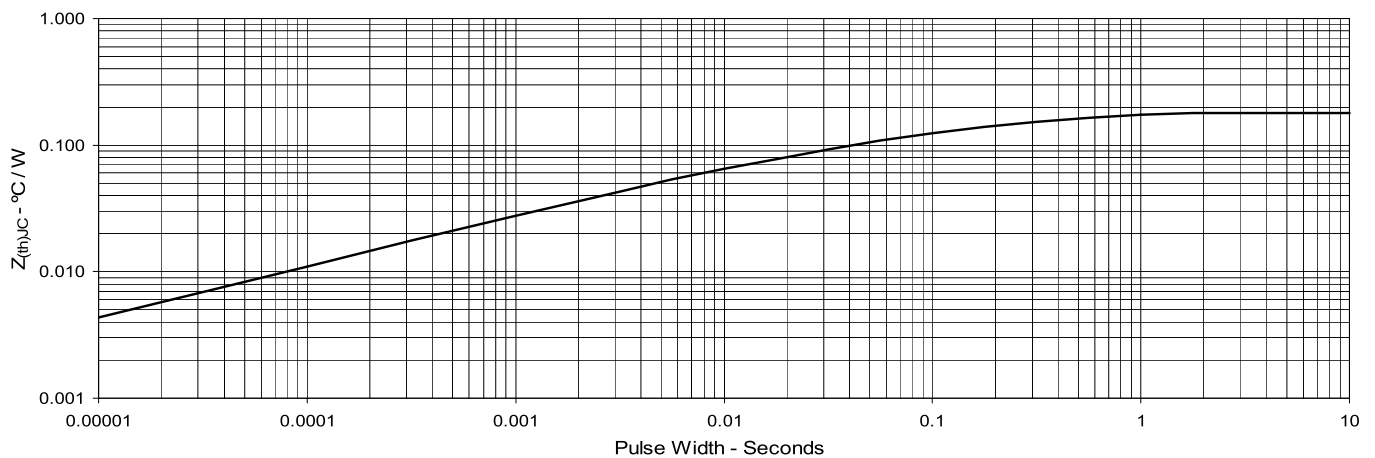
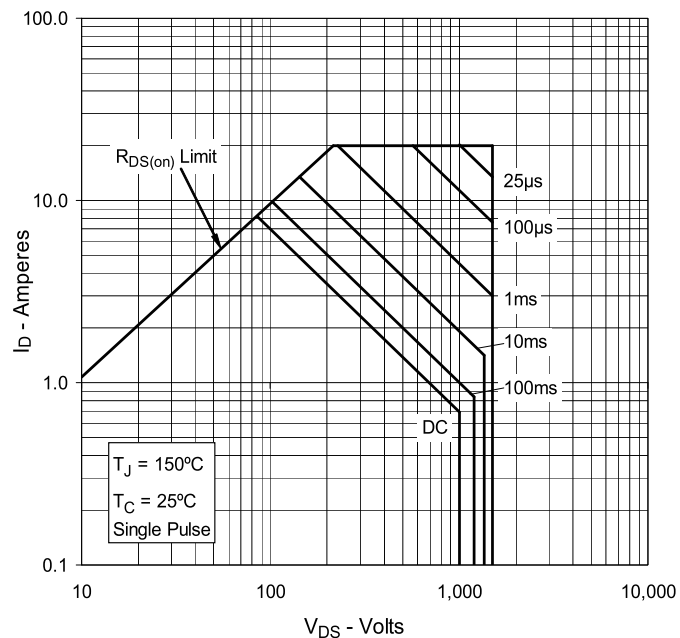


Fig. 11. Maximum Transient Thermal Impedance



**Fig. 12. Forward-Bias Safe Operating Area @
 $T_C = 25^\circ\text{C}$**



**Fig. 13. Forward-Bias Safe Operating Area
@ $T_C = 60^\circ\text{C}$**

